

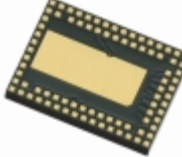


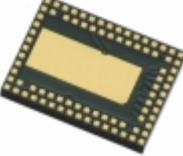
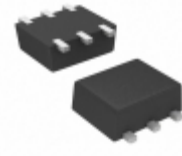
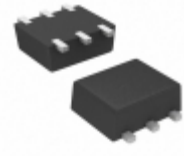

	<h2>SI1035X-T1-E3</h2>
	<p>Hersteller-Teilenummer: SI1035X-T1-E3</p> <p>Hersteller / Marke: Electro-Films (EFI) / Vishay</p> <p>Teil der Beschreibung: MOSFET N/P-CH 20V SOT563F</p> <p>Datenblätter:  SI1035X-T1-E3.pdf</p> <p>RoHs Status: Bleifrei / RoHS-konform</p> <p>Lagerzustand: New original, 237014 pcs Stock Available.</p> <p>Liefern von: Hong Kong</p> <p>Versandweg: DHL/Fedex/TNT/UPS/EMS</p>
<p>Image may be representation. See specs for product details.</p>	

Spezifikationen

Teilenummer	SI1035X-T1-E3
Hersteller	Electro-Films (EFI) / Vishay
Beschreibung	MOSFET N/P-CH 20V SOT563F
Kategorie	Diskrete Halbleiterprodukte > Transistoren-FETs ,
Teilstatus	237014 pcs Stock
detaillierte Beschreibung	Mosfet Array N and P-Channel 20V 180mA, 145mA
Serie	TrenchFET®
Betriebstemperatur	-55°C ~ 150°C (TJ)
Befestigungsart	Surface Mount
Leistung - max	250mW
Verpackung / Gehäuse	SOT-563, SOT-666
Supplier Device-Gehäuse	SC-89-6
Typ FET	N and P-Channel
FET-Merkmal	Logic Level Gate
Drain-Source-Spannung (Vdss)	20V
Strom - Ununterbrochener Abfluss (Id) bei 25 ° C	180mA, 145mA
Rds On (Max) @ Id, Vgs	5 Ohm @ 200mA, 4.5V
VGS (th) (Max) @ Id	400mV @ 250µA (Min)
Gate Charge (Qg) (Max) @ Vgs	0.75nC @ 4.5V
Eingabekapazität (Ciss) (Max) @ Vds	-
Verpackung	Cut Tape (CT)
Basisteilenummer	SI1035
Bleifreier Status / RoHS-Status	Lead free / RoHS Compliant
Feuchtigkeitsempfindlichkeitsniveau (MSL)	1 (Unlimited)
Andere Namen	SI1035X-T1-E3CT










SI1035X-T1-E3 ist neu im Original, Suche SI1035X-T1-E3 Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie SI1035X-T1-E3 Electro-Films (EFI) / Vishay mit Garantie und Vertrauen. Anfrage SI1035X-T1-E3: Info@Y-IC.com

Sie können auch interessiert sein:

 <p>SI1035X-T1-GE3 Electro-Films (EFI) / Vishay MOSFET N/P-CH 20V SC-89</p>	 <p>SI1035-B-GM3R Energy Micro (Silicon Labs) IC RF TXRX+MCU ISM<1GHZ 85-VFLGA</p>	 <p>SI1035X-T1 VISHAY SI1035X-T1 VISHAY</p>	 <p>SI1036-A-GMR Energy Micro (Silicon Labs) IC RF TXRX+MCU ISM<1GHZ 85-VFLGA</p>
 <p>SI1035-B-GM3 Energy Micro (Silicon Labs) IC RF TXRX+MCU ISM<1GHZ 85-VFLGA</p>	 <p>SI1035X-T1-GE3 Vishay / Siliconix MOSFET N/P-CH 20V SC-89</p>	 <p>SI1035X-T1-E3 Vishay / Siliconix MOSFET N/P-CH 20V SOT563F</p>	 <p>SI1035-A-GMR Energy Micro (Silicon Labs) IC RF TXRX+MCU ISM<1GHZ 85-VFLGA</p>

heiße Teile

Mehr

 SI1031X-T1-E3	 SI1031X-T1-E3	 SI1031X-T1-GE3	 SI1031X-T1-GE3	 SI1032R-T1
 SI1032R-T1-E3	 SI1032R-T1-E3	 SI1032R-T1-GE3	 SI1032R-T1-GE3	 SI1032X-T1
 SI1032X-T1-E3	 SI1032X-T1-E3	 SI1032X-T1-GE3	 SI1032X-T1-GE3	 SI1033X-T1
 SI1033X-T1-E3	 SI1033X-T1-E3	 SI1034CX-T1-GE3	 SI1034CX-T1-GE3	 SI1034X-T1
 SI1034X-T1-E3	 SI1034X-T1-E3	 SI1034X-T1-GE3	 SI1034X-T1-GE3	 SI1035X-T1
 SI1035X-T1-E3	 SI1035X-T1-GE3	 SI1035X-T1-GE3	 SI1039X-T1-E3	 SI1039X-T1-E3
 SI1040X-T1-E3	 SI1040X-T1-E3	 SI1040X-T1-GE3	 SI1040X-T1-GE3	 SI1041ADY
 SI1041DY-T1	 SI1041DY-T1-E3	 SI1045AB	 SI1045ADY-T1	 SI1046X-T1-E3
 SI1046X-T1-GE3	 SI1046X-T1-GE3	 SI1050X-T1-E3	 SI1050X-T1-E3	 SI1050X-T1-GE3
 SI1050X-T1-GE3	 SI1051X-T1-GE3	 SI1051X-T1-GE3	 SI1056X-T1-E3	 SI1056X-T1-E3

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